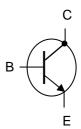


2N5681 - 2N5682

NPN SWITCHING TRANSISTORS

The 2N5681 and 2N5682 are silicon expitaxial planar PNP transistors in jedec TO-39 metal case. They are intended for use as drivers for high power transistors in general purpose, amplifier and switching circuit. The complementary PNP types are the 2N5679 and 2N5680 . Compliance to RoHS.



ABSOLUTE MAXIMUM RATINGS

Cymphal	Ratings		Val	I Incit	
Symbol			25681	2N5682	Unit
V _{CEO}	Collector-Emitter Voltage	I _B =0	100	120	V
V _{CBO}	Collector-Base Voltage	I _E =0	100	120	V
V_{EBO}	Emitter-Base Voltage	I _C =0	4		V
Ic	Collector Current		1		Α
I _B	Base Current		500		mA
P _D	Total Dawer Dissipation	$T_{amb} = 25^{\circ}C$	1		W
	Total Power Dissipation	$T_{case} = 25^{\circ}C$	10		
TJ	Junction Temperature		200		- °C
T _{Stg}	Storage Temperature range		-65 to +150		

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R _{thJ-a}	Thermal Resistance, Junction to ambient	175	°C/W
R _{thJ-c}	Thermal Resistance, Junction to case	17.5	°C/W



2N5681 - 2N5682

ELECTRICAL CHARACTERISTICS

Tj=25°C unless otherwise specified

Symbol	Ratings	Test Condition(s)		Min	Тур	Mx	Unit
I _{CBO}	Collector Cutoff Current	$V_{CB} = 100 \text{ V}, I_{E} = 0$	2N5679	-	-	1	μΑ
		$V_{CB} = 120 \text{ V}, I_{E} = 0$	2N5680				
I _{CEO}	Collector Cutoff	$V_{CE} = 70 \text{ V}, I_{B} = 0$	2N5679	_	-	10	μA
	Current	$V_{CE} = 80 \text{ V}, I_{B} = 0$	2N5680				
I _{CEV}	Collector Cutoff Current	$V_{CE} = 100 \text{ V}, V_{BE} = -1.5 \text{ V}$	2N5679	_	-	1	μA
		$V_{CE} = 120 \text{ V}, V_{BE} = -1.5 \text{ V}$	2N5680				
		$V_{CE} = 100 \text{ V}, V_{BE} = -1.5 \text{ V}$ $T_{C} = 150 ^{\circ}\text{C}$	2N5679	_	-	1	mA
		$V_{CE} = 120 \text{ V}, V_{BE} = -1.5 \text{ V}$ $T_{C} = 150 ^{\circ}\text{C}$	2N5680				
1	Emitter Cutoff Current	$V_{BE} = 4.0 \text{ V}, I_{C} = 0$	2N5679	_	-	1	μA
I _{EBO}			2N5680				
V	Collector Emitter Sustaining voltage (*)	I _C = 10 mA, I _B = 0	2N5679	100	-	-	V
$V_{CEO(sus)}$			2N5680	120	-	-	
	Collector-Emitter saturation Voltage (*)	$I_{\rm C} = 250 \text{mA}$	2N5679	-	-	0.6	V
V		$I_B = 25 \text{ mA}$	2N5680				
		$I_{\rm C} = 500 \text{mA}$	2N5679			1	
V _{CE(SAT)}		$I_B = 50 \text{ mA}$	2N5680		1	V	
		$I_C = 1 A$	2N5679	_	-	2	
		$I_B = 200 \text{ mA}$	2N5680				
W	Base-Emitter Voltage (*)	I _C = 250 mA, V _{CE} = 2 V	2N5679	-	-	1	V
V_{BE}			2N5680				
h _{FE}	DC Current Gain (*)	$I_C = 250 \text{ mA}, V_{CE} = 2 \text{ V}$	2N5679	40	-	150	
			2N5680				
		I _C = 1 A, V _{CE} = 2 V	2N5679 2N5680	5	-	-	
f _T	Transition frequency	$I_C = 100 \text{ mA}, V_{CE} = 10 \text{ V}$	2N5679	30	-	-	NALI-
		f = 10 MHz	2N5680				MHz
Сов	Output Capacitance	$I_E = 0, V_{CB} = 20 \text{ V}$	2N5679	-	-	50	nE
		f = 1MHz	2N5680				pF
h	Small Signal Current Gain	$I_C = 200 \text{ mA}, V_{CE} = 1.5 \text{ V}$	2N5679	40	-	-	-
h _{fe}		f = 1 kHz	2N5680	40			

^(*) Pulse Width \approx 300 μ s, Duty Cycle \angle 2.0%

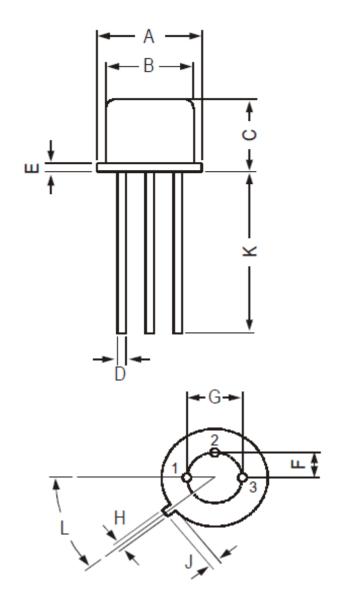


2N5681 - 2N5682

MECHANICAL DATA CASE TO-39

DIMENSIONS (mm)				
	min	max		
Α	8.50	9.39		
В	7.74	8.50		
С	6.09	6.60		
D	0.40	0.53		
Е	-	0.88		
F	2.41	2.66		
G	4.82	5.33		
Н	0.71	0.86		
J	0.73	1.02		
K	12.70	-		
L	42°	48°		

Pin 1 :	Emitter
Pin 2 :	Base
Pin 3 :	Collector
Case :	Collector



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